

**Claims:**

Please amend the claims as in the following listing:

- 1 1. (Original) A method for fabricating recording head sliders made from silicon  
2 substrates with SiO<sub>2</sub> overcoats, comprising:  
3 A) providing a Si wafer which has been fabricated with a SiO<sub>2</sub> overcoat;  
4 B) depositing a layer of DRIE-resistant material on said SiO<sub>2</sub> overcoat;  
5 C) depositing a patterned layer of RIE-resistant material on said layer of DRIE-  
6 resistant material to form a primary mask;  
7 D) etching by RIE through said primary mask to pattern said SiO<sub>2</sub> overcoat layer  
8 and said layer of DRIE-resistant material;  
9 E) removing said primary mask to expose said layer of DRIE-resistant material  
10 which has now been patterned to form a secondary mask;  
11 F) etching by DRIE through said secondary mask to cut said Si wafer into pieces;  
12 and  
13 G) removing said secondary mask.
- 1 2. (Original) The method of fabrication of claim 1, wherein:  
2 said RIE-resistant material is a metal.
- 1 3. (Original) The method of fabrication of claim 1, wherein:  
2 said RIE-resistant material is a transition metal.
- 1 4. (Currently amended) The method of fabrication of claim 1, wherein:  
2 said RIE-resistant material is chosen from the group consisting of Cu, NiFe, and  
3 [...(MORE)] transition metals.
- 1 5. (Currently amended) The method of fabrication of claim 1, wherein:  
2 said DRIE-resistant material is [chosen from the group consisting of] Al<sub>2</sub>O<sub>3</sub>.  
3 [and... (MORE)]
- 1 6. (Original) The method of fabrication of claim 1, wherein:  
2 said C) depositing a patterned layer of RIE-resistant material on said layer of  
3 DRIE-resistant material to form a primary mask comprises;  
4 i) applying, exposing and developing photoresist to create the pattern;  
5 ii) plating the layer of RIE-resistant material into the photo-resist pattern; and  
6 iii) stripping the photo-resist.
- 1 7. (Original) The method of fabrication of claim 6, wherein said C) depositing a  
2 patterned layer of RIE-resistant material on said layer of DRIE-resistant material to form  
3 a primary mask further comprises;  
4 applying a seed layer of RIE-resistant material before applying said photoresist.

- 1 8. (Original) The method of fabrication of claim 7, wherein:  
2 said D) etching by RIE further comprises:  
3 first sputter-etching away said seed layer of RIE-resistant material before  
4 RIE.
- 1 9. (Original) The method of fabrication of claim 1, wherein:  
2 said E) removing said primary mask is done by selective wet etching.
- 1 10. (Original) The method of fabrication of claim 1, wherein:  
2 said F) removing said secondary mask is done by selective wet etching.
- 1 11. (Original) A method for fabricating recording head sliders made from silicon  
2 substrates, comprising:  
3 A) producing a SiO<sub>2</sub> overcoat on said Si wafer;  
4 B) depositing a layer of DRIE-resistant material on said SiO<sub>2</sub> overcoat;  
5 C) depositing a RIE mask on said layer of DRIE-resistant material;  
6 D) etching by RIE through said RIE mask to pattern said SiO<sub>2</sub> overcoat layer and  
7 form a DRIE mask from said DRIE-resistant material;  
8 E) removing said RIE mask to expose said DRIE mask;  
9 F) etching by DRIE through said DRIE mask to cut said Si wafer; and  
10 G) removing said DRIE mask.
- 1 12. (Original) The method of fabrication of claim 11, wherein:  
2 said RIE-resistant material is a metal.
- 1 13. (Original) The method of fabrication of claim 11, wherein:  
2 said RIE-resistant material is a transition metal.
- 1 14. (Currently amended) The method of fabrication of claim 11, wherein:  
2 said RIE-resistant material is chosen from the group consisting of Cu, NiFe, and  
3 [...(MORE)] transition metals.
- 1 15. (Currently amended) The method of fabrication of claim 11, wherein:  
2 said DRIE-resistant material is [chosen from the group consisting of] Al<sub>2</sub>O<sub>3</sub>.  
3 [and... (MORE)]
- 1 16. (Original) The method of fabrication of claim 11, wherein:  
2 C) depositing a RIE mask on said layer of DRIE-resistant material comprises;  
3 i) applying, exposing and developing photoresist to create the pattern;  
4 ii) plating the layer of RIE-resistant material into the photo-resist pattern;  
5 and  
6 iii) stripping the photo-resist.
- 1 17. (Original) The method of fabrication of claim 16, wherein:

2 C) depositing a RIE mask on said layer of DRIE-resistant material further  
3 comprises:  
4 i) applying a seed layer of RIE-resistant material before applying said  
5 photoresist.

1 18. (Original) The method of fabrication of claim 17, wherein:  
2 said D) etching by RIE further comprises:  
3 first sputter-etching away said seed layer of RIE-resistant material before  
4 RIE.

1 19. (Original) The method of fabrication of claim 11, wherein:  
2 said E) removing said RIE mask is done by selective wet etching.

1 20. (Original) The method of fabrication of claim 11, wherein:  
2 said F) removing said DRIE mask is done by selective wet etching.